NSN 5961-01-199-2827

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-199-2827 **Inclosure Material:** Metal **Overall Length:** 0.570 inches **Terminal Length:** 1.000 inches **Overall Diameter:** 0.235 inches **Function For Which Designed:** Transient suppressor **End Application:** Radar bomb scoring set, an/tpq-43 Joint Electronic Device Engineering Council/jedec/case Outline Designation: **Electrode Internally-electrically Connected To Case:** Cathode **Mounting Method: Terminal Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 12.4 breakdown voltage, dc and 13.7 breakdown voltage, dc and 11.1 working peak reverse voltage **Current Rating Per Characteristic:** 200.00 amperes forward current, average preset **Power Rating Per Characteristic:** 1.0 watts small-signal input power, common-collector horsepower metric **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius junction **Test Data Document:** 81349-mil-s-19500 specification (includes engineering type bulletins, brochures, etc., that reflect specification type data in specification format; excludes commercial catalogs, industry directories, and similar trade publications, reflecting general type data on certain environmental and performance requirements and test conditions that are shown as "typical", "average", "", etc.). **Terminal Type And Quantity:** 2 uninsulated wire lead **Specification Data:** 81349-mil-s-19500/500 government specification Shelf Life: N/a **Unit Of Measure:**

Fiig: A110a0

No

Demilitarization: